

# 2SD1739

## Silicon PNP Triple-Diffused Planar Type

### Horizontal Deflection Output

#### ■ Features

- High breakdown voltage, high reliability
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

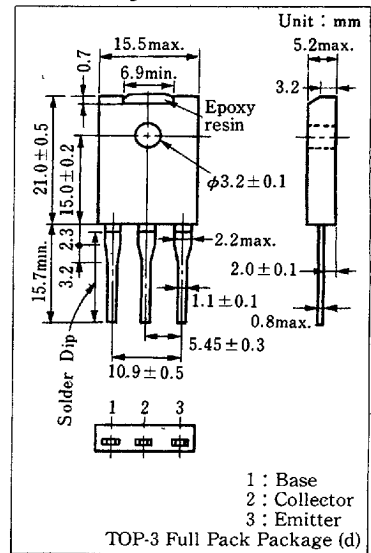
#### ■ Absolute Maximum Ratings (T<sub>c</sub>=25°C)

Item	Symbol	Value	Unit	
Collector-base voltage	V <sub>CB0</sub>	1500	V	
Collector-emitter voltage	V <sub>CES</sub>	1500	V	
	V <sub>CEO</sub>	700	V	
Emitter-base voltage	V <sub>EBO</sub>	7	V	
Peak collector current	I <sub>CP</sub>	18	A	
Collector current	I <sub>C</sub>	6	A	
Base current	I <sub>B</sub>	2.5	A	
Collector power dissipation	P <sub>C</sub>	T <sub>c</sub> = 25°C	100	W
		T <sub>a</sub> = 25°C	3	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 ~ +150	°C	

#### ■ Electrical Characteristics (T<sub>c</sub>=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> = 750 V, I <sub>E</sub> = 0			10	μA
		V <sub>CB</sub> = 1500 V, I <sub>E</sub> = 0			1	mA
Emitter-base voltage	V <sub>EBO</sub>	I <sub>E</sub> = 1mA, I <sub>C</sub> = 0	7			V
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 1 A	6		30	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 5 A, I <sub>B</sub> = 1.2 A			8	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 5 A, I <sub>B</sub> = 1.2 A			1.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1A, f = 0.5MHz		2		MHz
Storage time (L load)	t <sub>stg</sub>	I <sub>C</sub> = 5 A, I <sub>B1</sub> = 1.2 A			10	μs
Fall time (L load)	t <sub>f</sub>	I <sub>B2</sub> = -1.2 A, L <sub>B</sub> = 5 μH			0.8	μs
Storage time (R load)	t <sub>stg</sub>	I <sub>C</sub> = 5 A, I <sub>B1</sub> = 1 A		1.5		μs
Fall time (R load)	t <sub>f</sub>	I <sub>B2</sub> = -2 A, V <sub>CC</sub> = 200 V		0.2		μs

#### ■ Package Dimensions



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